

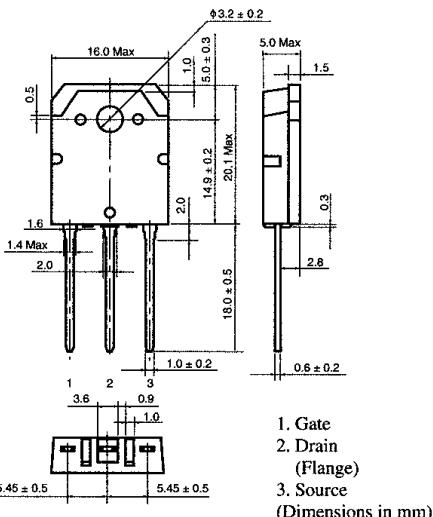
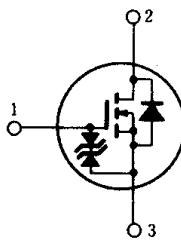
# 2SK695

## SILICON N-CHANNEL MOS FET

高速度電力スイッチング

### ■ 特長

- オン抵抗が低い。
- スイッチング速度が速い。
- 駆動電力が小さい。
- 2次降伏がない。
- スイッチングレギュレータ、  
DC-DCコンバータなどに最適。



1. Gate  
2. Drain  
(Plange)  
3. Source  
(Dimensions in mm)

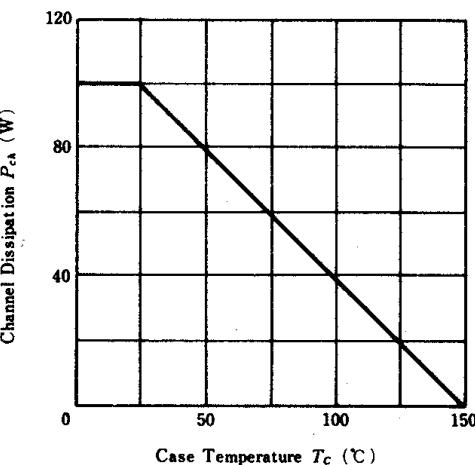
(TO-3P)

### ■ ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DSS}$	800	V
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Drain Current	$I_D$	5	A
Drain Peak Current	$I_{D(\text{pulse})}^*$	15	A
Body-Drain Diode	$I_{DR}$	5	A
Reverse Drain Current			
Channel Dissipation	$P_{ch}^{**}$	100	W
Channel Temperature	$T_{ch}$	150	°C
Storage Temperature	$T_{stg}$	-55 ~ +150	°C

\*PW≤10μs, duty cycle≤1%   \*\*Value at  $T_c = 25^\circ\text{C}$

### POWER VS. TEMPERATURE DERATING



### ■ ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 10\text{mA}, V_{GS} = 0$	800	—	—	V
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu\text{A}, V_{DS} = 0$	$\pm 20$	—	—	V
Gate-Source漏電流	$I_{GSS}$	$V_{GS} = \pm 16\text{V}, V_{DS} = 0$	—	—	$\pm 10$	$\mu\text{A}$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 640\text{V}, V_{GS} = 0$	—	—	250	$\mu\text{A}$
Gate-Source Cutoff Voltage	$V_{GS(off)}$	$I_D = 1\text{mA}, V_{DS} = 10\text{V}$	2.0	—	4.0	V
Static Drain-Source on State Resistance	$R_{DS(on)}$	$I_D = 3\text{A}, V_{GS} = 10\text{V}^*$	—	2.0	3.0	$\Omega$
Forward Transfer Admittance	$ y_{f(s)} $	$I_D = 3\text{A}, V_{DS} = 20\text{V}^*$	1.5	2.5	—	S
Input Capacitance	$C_{iss}$	$V_{DS} = 10\text{V}, V_{GS} = 0, f = 1\text{MHz}$	—	1150	—	pF
Output Capacitance	$C_{oss}$		—	610	—	pF
Reverse Transfer Capacitance	$C_{res}$		—	420	—	pF
Turn-on Delay Time	$t_{d(on)}$	$I_D = 3\text{A}, V_{GS} = 10\text{V}, R_L = 10\Omega$	—	20	—	ns
Rise Time	$t_r$		—	155	—	ns
Turn-off Delay Time	$t_{d(off)}$		—	120	—	ns
Fall Time	$t_f$		—	120	—	ns
Body-Drain Diode Forward Voltage	$V_{DF}$	$I_F = 5\text{A}, V_{GS} = 0$	—	1.0	—	V
Body-Drain Diode Reverse Recovery Time	$t_{rr}$	$I_F = 5\text{A}, V_{GS} = 0, dI_F/dt = 100\text{A}/\mu\text{s}$	—	800	—	ns

\*Pulse Test